



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



12V PNP SILICON LOW SATURATION SWITCHING TRANSISTOR AND SCHOTTKY DIODE

SUMMARY

Transistor: $V_{CE0} = -12V$, $I_C = -1.25A$

Schottky Diode: $V_R = 40V$; $I_C = 0.5A$

DESCRIPTION

A PNP transistor and a Schottky Barrier diode contained in a single 6 leaded SOT23 package.

FEATURES

- Low Saturation Transistor
- High Gain - 300 minimum
- Low V_F , fast switching Schottky

APPLICATIONS

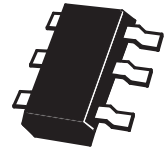
- Mobile telecomms, PCMCIA & SCSI
- DC-DC Conversion

ORDERING INFORMATION

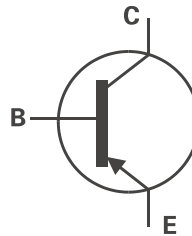
DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXTS1000E6TA	7	8mm embossed	3000 units
ZXTS1000E6TC	13	8mm embossed	10000 units

DEVICE MARKING

1000



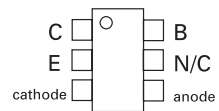
SOT23-6



Cathode



Anode



Top View

ZXTS1000E6

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Transistor			
Collector-Base Voltage	V_{CBO}	-12	V
Collector-Emitter Voltage	V_{CEO}	-12	V
Emitter-Base Voltage	V_{EBO}	-5	V
Continuous Collector Current	I_C	-1.25	A
Schottky Diode			
Continuous Reverse Voltage	V_R	40	V
Forward Current	I_F	0.5	A
Non Repetitive Forward Current $t \leq 100\mu s$	I_{FSM}	6.75	A
$t \leq 10ms$		3	A
Package			
Power Dissipation at $T_{amb}=25^\circ C$ single die "on" both die "on"	P_D	0.725	W
		0.885	W
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ C$
Junction Temperature	T_j	125	$^\circ C$

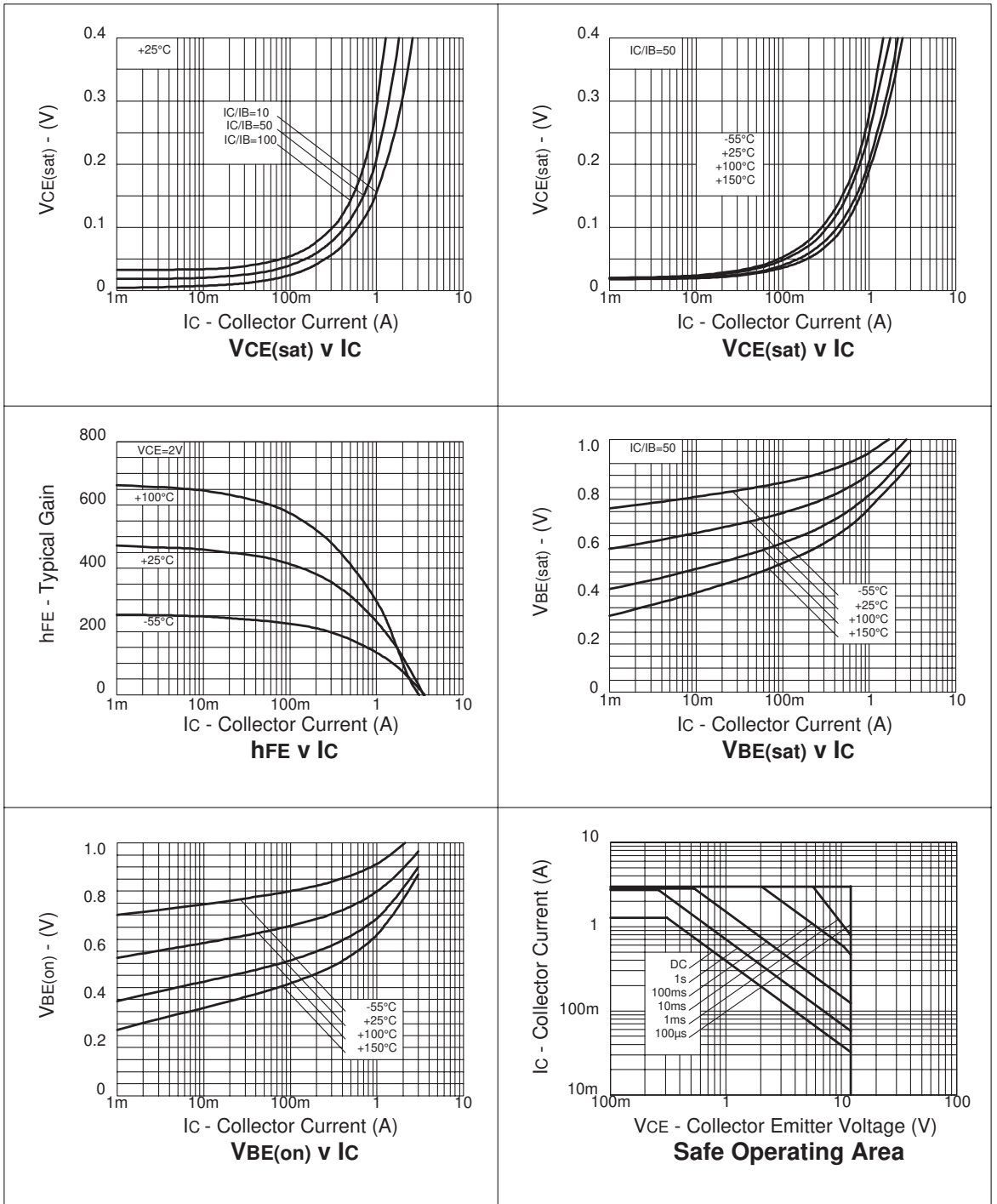
THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a) single die "on"	$R_{\theta JA}$	138	$^\circ C/W$
both die "on"	$R_{\theta JA}$	113	$^\circ C/W$

NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

TRANSISTOR TYPICAL CHARACTERISTICS



ZXTS1000E6

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

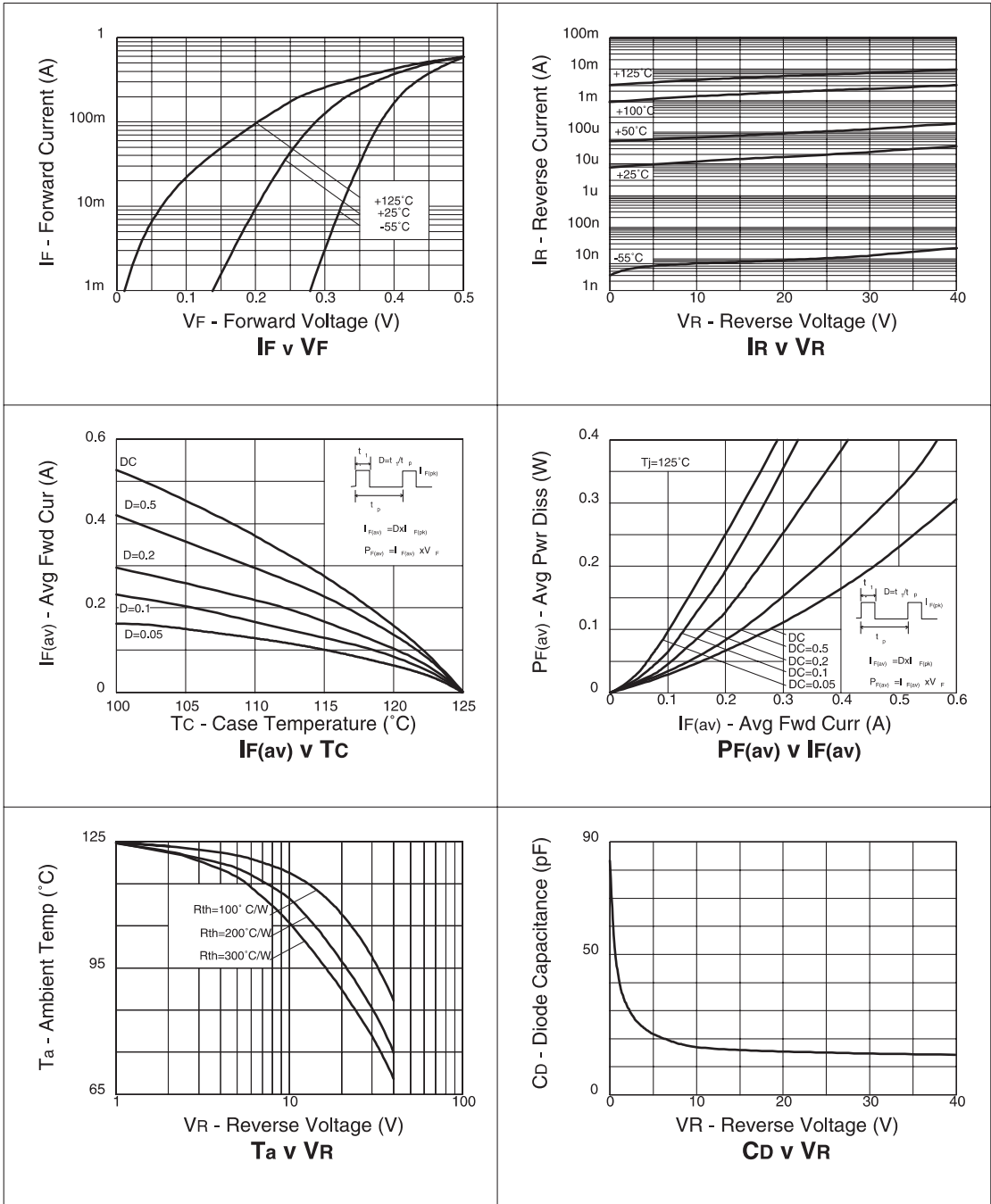
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
TRANSISTOR ELECTRICAL CHARACTERISTICS						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-12			V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-12			V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-10	nA	$V_{CB} = -10\text{V}$
Emitter Cut-Off Current	I_{EBO}			-10	nA	$V_{EB} = -4\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			-10	nA	$V_{CES} = -10\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-25 -55 -110 -160 -185	-40 -100 -175 -215 -240	mV mV mV mV mV	$I_C = -0.1\text{A}, I_B = -10\text{mA}^*$ $I_C = -0.25\text{A}, I_B = -10\text{mA}^*$ $I_C = -0.5\text{A}, I_B = -10\text{mA}^*$ $I_C = -1\text{A}, I_B = -50\text{mA}^*$ $I_C = -1.25\text{A}, I_B = -100\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-990	-1100	mV	$I_C = -1.25\text{A}, I_B = -100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-850	-1000	mV	$I_C = -1.25\text{A}, V_{CE} = 2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	300 300 200 125 75 30	490 450 340 250 140 80			$I_C = -10\text{mA}, V_{CE} = -2\text{V}^*$ $I_C = -0.1\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -0.5\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -1.25\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -2\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -3\text{A}, V_{CE} = -2\text{V}^*$
Transition Frequency	f_T		220		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}		15		pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Turn-On Time	$t_{(on)}$		50		ns	$V_{CC} = -10\text{V}, I_C = -1\text{A}$ $I_{B1} = I_{B2} = -100\text{mA}$
Turn-Off Time	$t_{(off)}$		135		ns	

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS

Reverse Breakdown Voltage	$V_{(BR)R}$	40	60		V	$I_R = 200\mu\text{A}$
Forward Voltage	V_F		270 300 370 425 550 640 810	300 350 460 550 670 780 1050	mV mV mV mV mV mV mV	$I_F = 50\text{mA}^*$ $I_F = 100\text{mA}^*$ $I_F = 250\text{mA}^*$ $I_F = 500\text{mA}^*$ $I_F = 750\text{mA}^*$ $I_F = 1000\text{mA}^*$ $I_F = 1500\text{mA}^*$
Reverse Current	I_R		15	40	μA	$V_R = 30\text{V}$
Diode Capacitance	C_D		20		pF	$f = 1\text{MHz}, V_R = 30\text{V}$
Reverse Recovery Time	t_{rr}		10		ns	switched from $I_F = 500\text{mA}$ to $I_R = 500\text{mA}$ Measured at $I_R = 50\text{mA}$

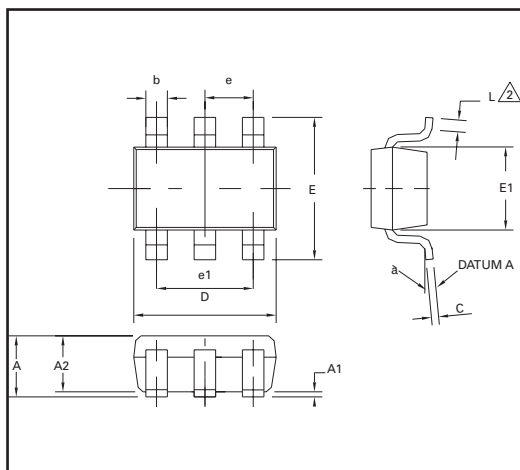
*Measured under pulsed conditions.

DIODE TYPICAL CHARACTERISTICS

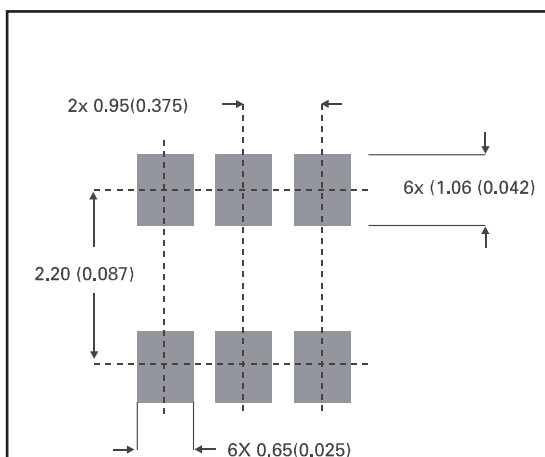


ZXTS1000E6

PACKAGE DIMENSIONS



PAD LAYOUT DETAILS



DIM	Millimetres		Inches	
	Min	Max	Min	Max
A	0.90	1.45	0.35	0.057
A1	0.00	0.15	0	0.006
A2	0.90	1.30	0.035	0.051
b	0.35	0.50	0.014	0.019
C	0.09	0.20	0.0035	0.008
D	2.80	3.00	0.110	0.118
E	2.60	3.00	0.102	0.118
E1	1.50	1.75	0.059	0.069
L	0.10	0.60	0.004	0.002
e	0.95 REF		0.037 REF	
e1	1.90 REF		0.074 REF	
L	0°	10°	0°	10°

ZETEX Zetex plc.
 Fields New Road, Chadderton, Oldham, OL9-8NP, United Kingdom.
 Telephone: (44)161 622 4422 (Sales), (44)161 622 4444 (General Enquiries)
 Fax: (44)161 622 4420

Zetex GmbH
 Streitfeldstraße 19
 D-81673 München
 Germany
 Telefon: (49) 89 45 49 49 0
 Fax: (49) 89 45 49 49 49

Zetex Inc.
 47 Mall Drive, Unit 4
 Commack NY 11725
 USA
 Telephone: (631) 543-7100
 Fax: (631) 864-7630

Zetex (Asia) Ltd.
 3701-04 Metroplaza, Tower 1
 Hing Fong Road,
 Kwai Fong, Hong Kong
 Telephone: (852) 26100 611
 Fax: (852) 24250 494

These are supported by
 agents and distributors in
 major countries world-wide
 © Zetex plc 2000
www.zetex.com

This publication is issued to provide outline information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contract or be regarded as a representation relating to the products or services concerned. The Company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.

ZETEX

ISSUE 1 - NOVEMBER 2000